

Magnetic Sensor IC

Dual Outputs for both S and N-pole Low Power Hall-Effect Sensor IC



AS1820AOD

● General Description

Using low power CMOS process, the AS1820AOD is designed for low power, high performance unipolar detection dual output hall-effect application, such as cover switch, contactless switch, solid state switch and lid close sensor etc battery operation. The hall IC integrated an on-chip hall voltage generator for magnetic sensing, a comparator that amplifiers the hall voltage, a chopper amplifier, a Schmitt trigger to provide switching hysteresis for noise rejection, and two complementary output.

The total power consumption of AS1820AOD is typically less than 4.0uA at 1.8V power supply. AS1820AOD is designed to respond to alternating North and South poles. While the magnetic flux density (B) is larger than operate point (B_{OP}), the output will be turned on (low), the output is held until the magnetic flux density (B) is lower than release point (B_{RP}), then turn off (high-Z).

The device is available in DFN1014-4L and DFN1010-4L Package and is rated over the -40°C to 85°C . The all packages are RoHS and Green compliant.

● Features

- Input Voltage Range : 1.65V to 5.5V
- Micro-power consumption ideal for battery power applications
- Unipolar Operation, dual output
- Very high sensitivity hall sensor
- Low Power CMOS process technology
- Chopper stabilization amplifier stage
- Magnetic Sensitivity (typical)
 $B_{OPS}=28\text{Gauss}$, $B_{RPS}=18\text{Gauss}$
 $B_{OPN}= -28\text{Gauss}$, $B_{RPN}= -18\text{Gauss}$
- Good RF noise immunity
- Open Drain output
- Small Solution Size
- RoHS & Green Compliant
- DFN1014-4L & DFN1010-4L Packages
- -40°C to $+85^{\circ}\text{C}$ Temperature Range

● Applications

- Cover switch in clam-shell cellular phones
- Cover switch in Notebook, PC/PAD
- Contact-less switch in consumer products
- Solid State Switch
- Handheld Wireless Handset Awake Switch
- Lid close sensor for battery-powered device
- Magnet proximity sensor for reed switch replacement in low duty cycle applications
- DV, DSC, and White Goods

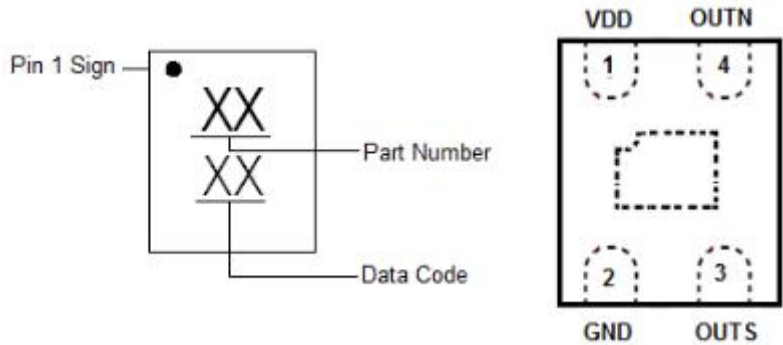
■ Ordering Information



Part Number	B_{OP} (Gauss)	B_{RP} Gauss)	Package Type	Package Qty	Temperature	Eco Plan	Lead
AS1820AODDRN	$\pm 28\text{Gauss}$	$\pm 18\text{Gauss}$	DFN1014-4L	7-in reel 3000pcs/reel	$-40\sim 85^{\circ}\text{C}$	Green	Cu
AS1820AODD1RN	$\pm 28\text{Gauss}$	$\pm 18\text{Gauss}$	DFN1010-4L	7-in reel 10000pcs/reel	$-40\sim 85^{\circ}\text{C}$	Green	Cu

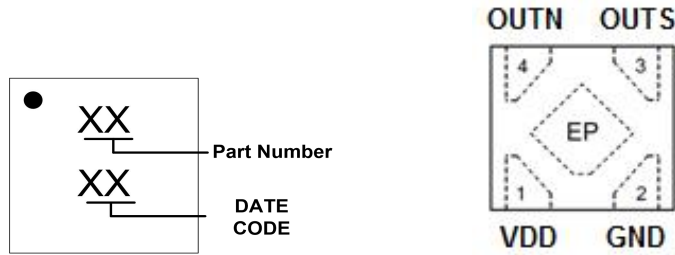
■ Marking & Pin Assignment

DFN1014-4L



Pin Name	Pin No.	I/O	Pin Function
	DFN1014-4L		
VDD	1	P	Input Power Supply.
GND	2	P	Ground.
OUTS	3	O	Output Pin for South Pole.
OUTN	4	O	Output Pin for North Pole.

DFN1010-4L



Pin Name	Pin No.	I/O	Pin Function
	DFN1010-4L		
VDD	1	P	Input Power Supply.
GND	2	P	Ground.
OUTS	3	O	Output Pin for South Pole.
OUTN	4	O	Output Pin for North Pole.

■ Typical Application Circuit

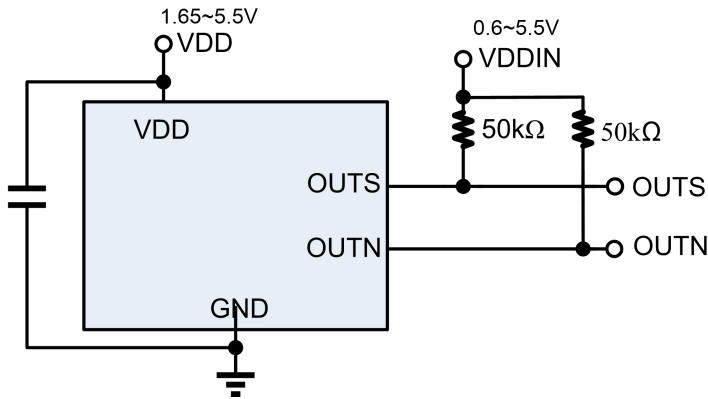


Figure 1, Typical Application Circuit of AS1820AOD

■ Block Diagram

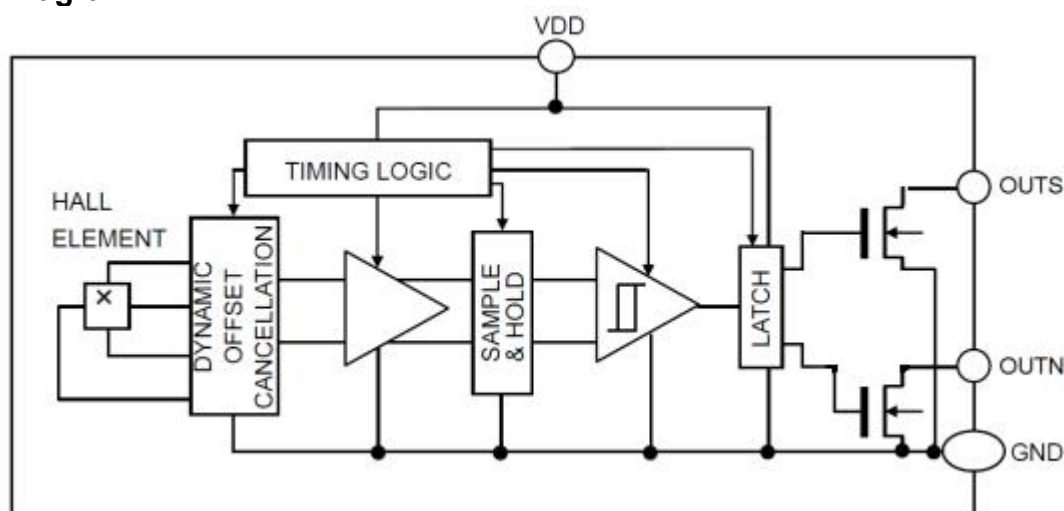


Figure 2, Block Diagram of AS1820AOD

■ Absolute Maximum Ratings¹ (T_A=25°C, unless otherwise noted)

Parameter	Symbol	Rating	Unit
V _{DD} Pin to GND	V _{DD}	-0.3 to 6.5	V
Output Pin to GND	V _{OUTPUT}	-0.3 to V _{DD} +0.3	V
Max. Continuous Output Current	I _{OUTMAX}	2.0	mA
Magnetic Flux Density	B	Unlimited	Gauss
ESD (HBM)	HBM	8000	V
ESD (MM)	MM	700	V
ESD (CDM)	CDM	2000	V
Storage Temperature Range	T _S	-55 to +150	°C
Operating Junction Temperature Range	T _{OP}	-40 to +150	°C

■ Recommended Operating Conditions²

Parameter	Symbol	Rating	Unit
V _{DD} Pin to GND	V _{DD}	1.6 to 5.5	V
Continuous Output Current	I _{OUT}	1.0	mA
Operating Temperature Range	T _{OP}	-40 to +85	°C

Note: 1: Stresses above those listed in absolute maximum ratings may cause permanent damage to the device. Functional operation at conditions other than the operating conditions specified is not implied. Only one absolute maximum rating should be applied at any one time. 2: The device is not guaranteed to function outside of its operating conditions.

■ Electrical Characteristics

($T_A = -40$ to $+85^\circ\text{C}$ unless otherwise noted. Typical values are at $T_A = +25^\circ\text{C}$, $V_{DD} = 1.8\text{V}$)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{DD}	Input Voltage		1.65	1.8	5.5	V
$I_{DD}(\text{AVG})$	Supply Current	Average supply current, $T_A = 25^\circ\text{C}$, $V_{DD} = 1.8\text{V}$, no magnetic field	-	4.0	6.0	μA
T_{awake}	Awake Time		75	150	200	μs
T_{period}	Period		25	50	100	ms
V_{OL}	Output On Voltage (Low side)	$I_{OUT} = +1\text{mA}$	-	0.1	0.2	V
Magnetic Para.						
B_{OPS}	Magnetic Operating Point		16	28	39	Gauss
B_{OPN}			-39	-28	-16	Gauss
B_{RPS}	Magnetic Release Point		10	18	30	Gauss
B_{RPN}			-30	-18	-10	Gauss
B_{HYS}	Hysteresis Window		-	10	-	Gauss

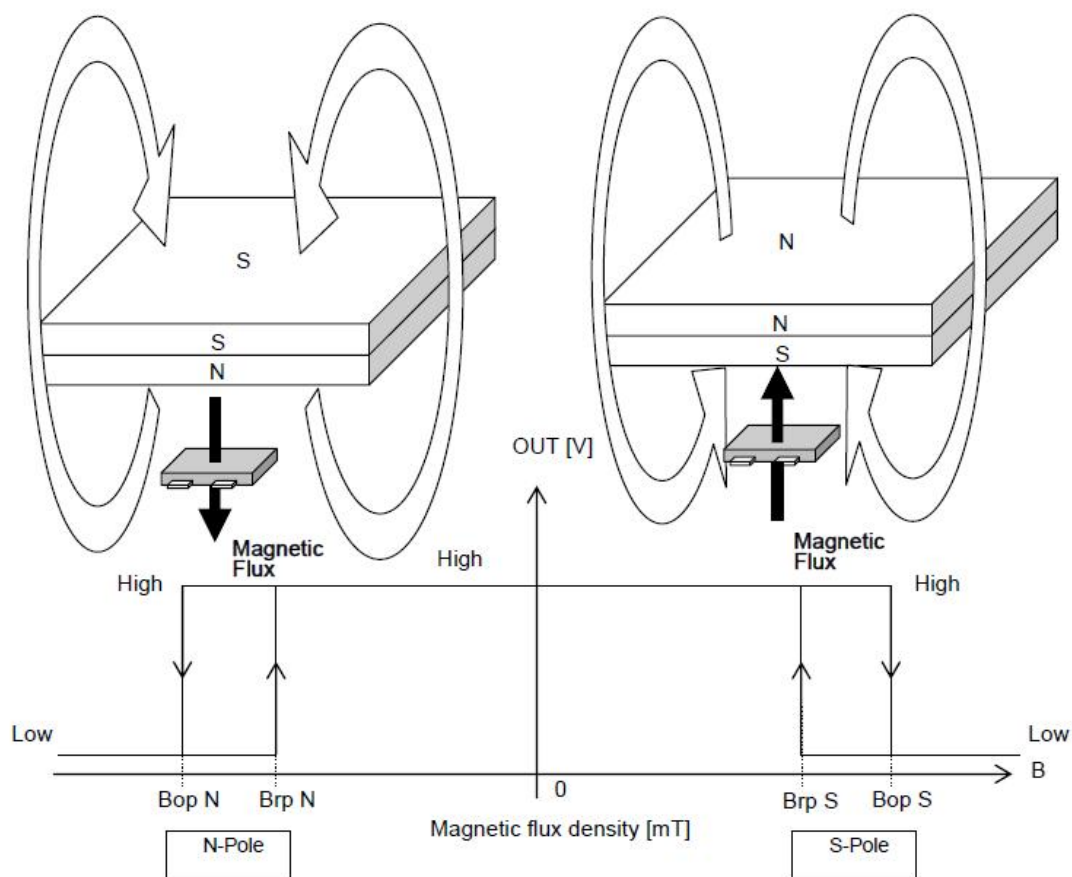
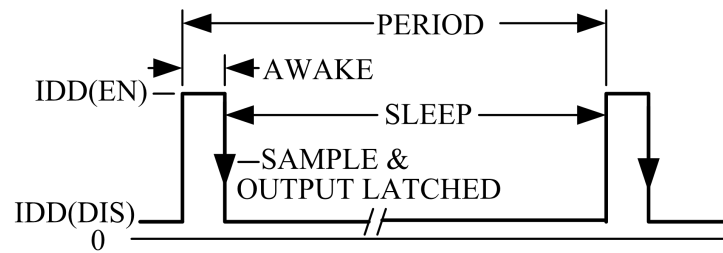


Figure 3, Magnetic Operation Characteristic of AS1820AOD

■ Function Description



Micro-power Operation

Internal timing circuitry activates the sensor for 150 μ s and deactivates it for the remainder of the period (50ms). A short "awake" time allows for stabilization prior to the sensor sampling and data latching on the falling edge of the timing pulse. The output during the "sleep" time is latched in the last sampled state. The supply current is not affected by the output state.

Chopper-Stabilized Technique

The Hall element can be considered as a resistor array similar to a Wheatstone bridge. A large portion of the offset is a result of the mismatching of these resistors. These devices use a proprietary dynamic offset cancellation technique, with an internal high-frequency clock to reduce the residual offset voltage of the Hall element that is normally caused by device over-molding, temperature dependencies, and thermal stress. The chopper-stabilizing technique cancels the mismatching of the resistor circuit by changing the direction of the current flowing through the Hall plate using CMOS switches and Hall voltage measurement taps, while maintains the Hall voltage signal that is induced by the external magnetic flux. The signal is then captured by a sample-and-hold circuit and further processed using low-offset bipolar circuitry. This technique produces devices that have an extremely stable quiescent Hall output voltage, are immune to thermal stress, and have precise recoverability after temperature cycling. A relatively high sampling frequency is used for faster signal processing capability can be processed.

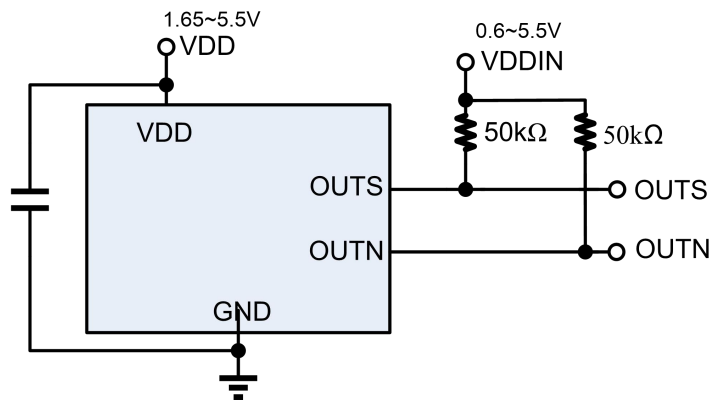
Magnetic Field Detection Mechanism

The Hall IC cannot detect magnetic fields that run horizontal to the package top layer. Be certain to configure the Hall IC so that the magnetic field is perpendicular to the top layer.

Operation

The output of this device switches low (turns on) when a magnetic field perpendicular to the Hall sensor exceeds the operate point B_{OPS} (or is less than B_{OPN}). After turn-on, the output is capable of sinking up to 1mA and the output voltage is $V_{OUT(ON)}$. When the magnetic field is reduced below the release point B_{RPS} (or increased above B_{RPN}), the device output switches high (turns off). The difference between the magnetic operates and release points are the hysteresis (B_{HYS}) of the device. This built-in hysteresis allows clean switching of the output even in the presence of external mechanical vibration and electrical noise.

■ Applications:



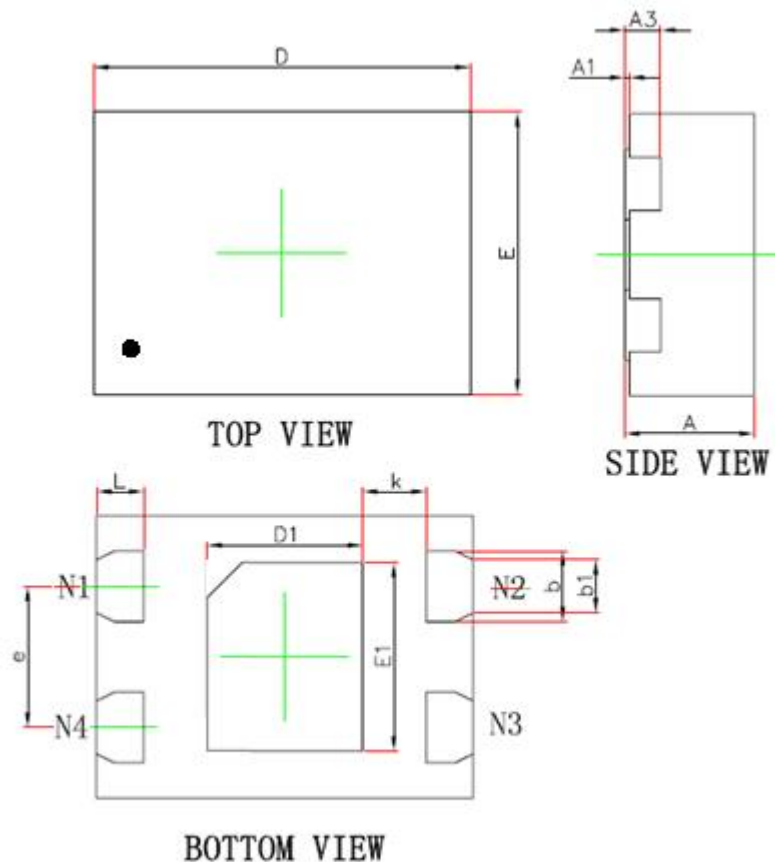
AS1820AOD's pole-independent sensing technique allows for operation with either a north or south poles magnet orientation, enhancing the manufacturability of the device. The state-of-the-art technology provides the same output polarity for either pole face.

C1 serves two purposes: minimizing ripples on the input voltage and enhancing immunity from RF transmission noises within close proximity. Recommended values are between 0.1 μ F and 1 μ F. The larger the capacitance, the better the noise immunity is for the AS1820AOD.

It is strongly recommended that an external bypass capacitor be connected (in close proximity to the Hall sensor) between the supply and ground of the device to reduce both external noise and noise generated by the chopper-stabilization technique. This is especially true due to the relatively high impedance of battery supplies. The simplest form of magnet that will operate these devices is a bar magnet with either pole near the branded surface of the device.

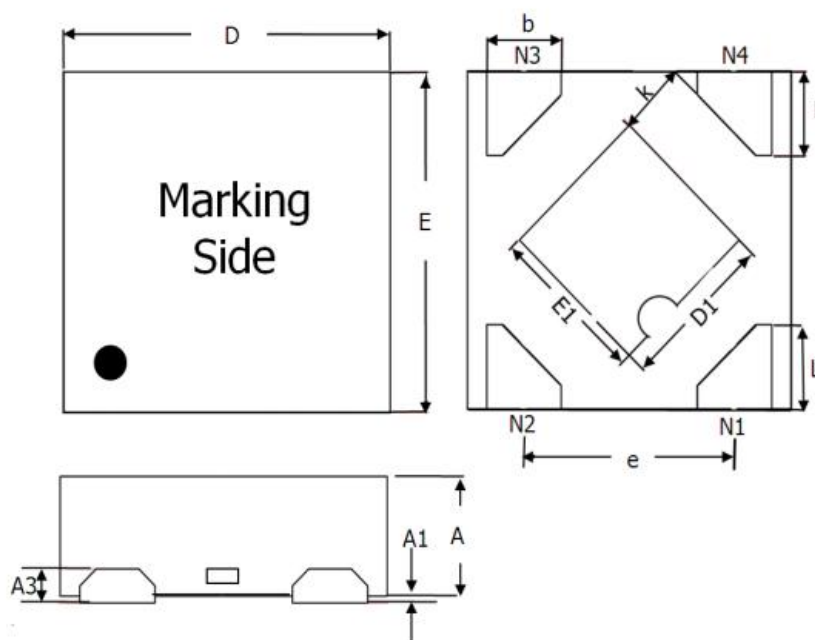
■ Package Information

DFN1014-4L:



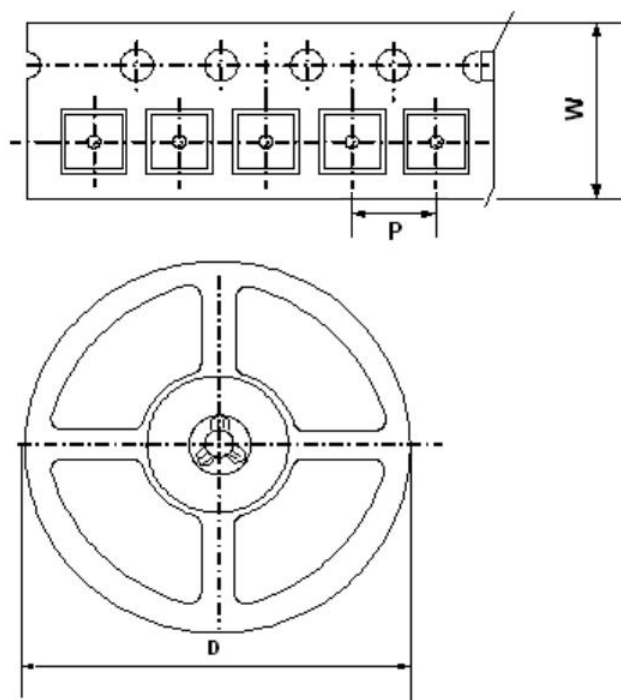
Symbol	Dimensions In Millimeters			Dimensions In Inches		
	Min.	Nom.	Max.	Min.	Nom.	Max.
A	0.320	0.370	0.400	0.013	0.014	0.016
A1	0.000	-	0.050	0.000	-	0.002
A3	0.102 (BSC)			0.004 (BSC)		
D	1.400 (BSC)			0.055 (BSC)		
E	1.000 (BSC)			0.039 (BSC)		
D1	0.500	0.600	0.700	0.020	0.024	0.028
E1	0.700	0.800	0.900	0.028	0.031	0.035
L	0.150	0.200	0.250	0.006	0.008	0.010
b	0.170	0.220	0.270	0.007	0.009	0.011
b1	0.170	0.220	0.270	0.007	0.009	0.011
e	0.500 (BSC)			0.020 (BSC)		
k	0.200 (BSC)			0.008 (BSC)		

DFN1010-4L:

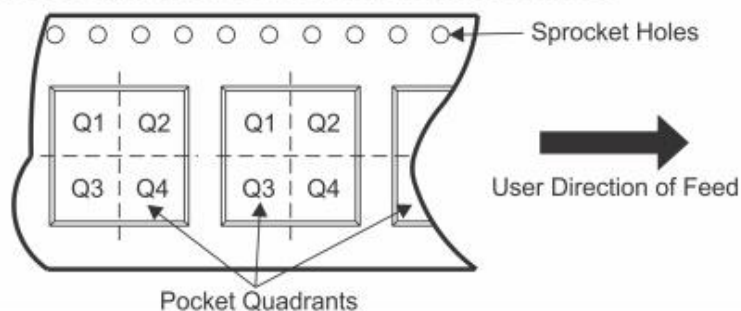


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.340	0.400	0.014	0.016
A1	0.000	0.050	0.000	0.002
A3	0.152 BSC		0.006 BSC	
D	0.950	1.050	0.038	0.042
E	0.950	1.050	0.038	0.042
D1	0.450	0.550	0.018	0.022
E1	0.450	0.550	0.018	0.022
k	0.211 BSC		0.008 BSC	
b	0.180	0.280	0.0072	0.0112
e	0.625 BSC		0.025 BSC	
L	0.200	0.300	0.008	0.012

■ Tape and Reel Information



QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Device	Package Type	SPQ	Carrier Width (W)	Pitch(P)	Reel Size(D)	Pin1 Quadrant
AS1820AODDRN	DFN1014-4L	3000pcs	8.0±0.1 mm	4.0±0.1 mm	180±1 mm	Q2
AS1820AODD1RN	DFN1010-4L	10000pcs	8.0±0.1 mm	2.0±0.1 mm	180±1 mm	Q1

*All dimensions are nominal